



#### **100V N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Product Summary**

V	Park	ID	
V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	T <sub>A</sub> = +25°C	
1001/	125mΩ @ V <sub>GS</sub> = 10V	4.0A	
100V	$150m\Omega @ V_{GS} = 6.0V$	3.7A	

#### Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### Applications

- DC Motor Control
- DC-AC Inverters

#### **Features and Benefits**

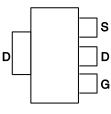
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

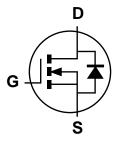
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)



Top View



Pin Out - Top View



Equivalent Circuit

#### Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
ZXMN10A25GTA	Standard	SOT223	1,000 / Tape & Reel

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

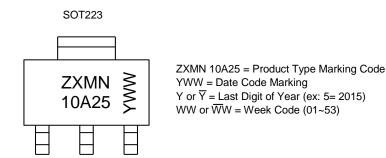
2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**

Notes:





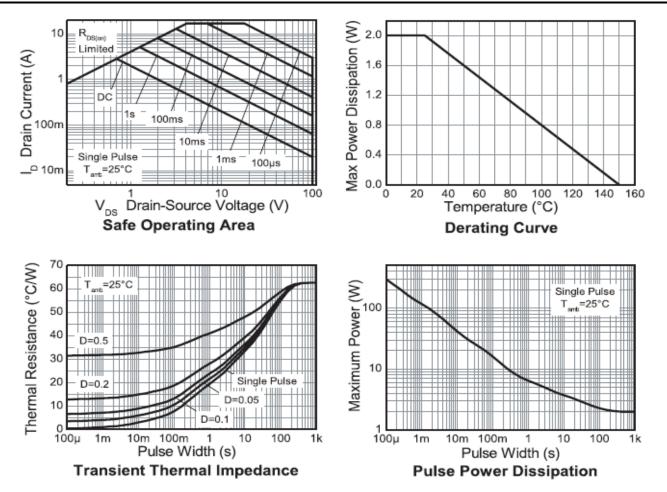
# Maximum Ratings ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	100	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current, V_{GS} = 10V, t $\leq$ 10 sec	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	4.0 3.2	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	T <sub>A</sub> = +25°C	ID	2.9	А
Maximum Continuous Body Diode Forward Current (Note 5)	Is	5.4	А	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	17	А	
Pulsed Source Current (10µs pulse, duty cycle = 1%)		I <sub>SM</sub>	17	А

# Thermal Resistance (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5), TA = +25°C	6	2.0	W
Linear Derating Factor	PD	16	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ ext{ heta}JA}$	62.5	°C/W
Total Power Dissipation (Note 5), TA = +25°C, t $\leq$ 10 seconds Linear Derating Factor	PD	3.9 31	W mW/°C
Thermal Resistance, Junction to Ambient, t $\leq$ 10 seconds (Note 5)	R <sub>0JA</sub>	32	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





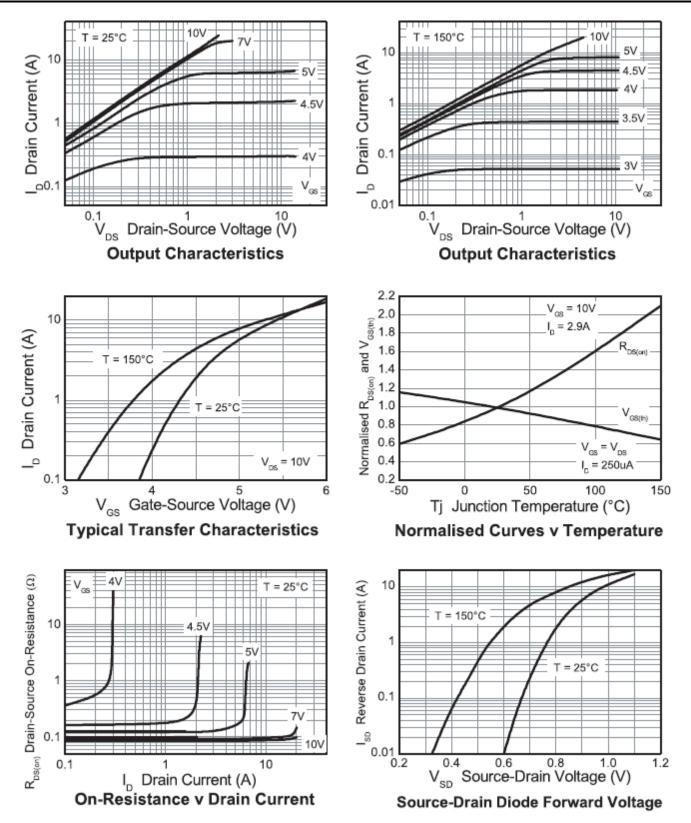
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	—	0.5	μA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)					•	·	
Gate Threshold Voltage	V <sub>GS(th)</sub>	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	D	_	—	125		$V_{GS} = 10V, I_D = 2.9A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	—	150	mΩ	$V_{GS} = 6.0V, I_D = 2.6A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	7.3	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 2.9A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.85	0.95	V	$V_{GS} = 0V, I_{S} = 4.0A$	
DYNAMIC CHARACTERISTICS (Note 7)						-	
Input Capacitance	C <sub>iss</sub>	—	859	_		V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1.0MHz	
Output Capacitance	C <sub>oss</sub>	_	57	—	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	33	_			
Total Gate Charge	Qg	_	9.6	—	nC	$V_{DS} = 50V, V_{GS} = 5.0V, I_D = 2.9A$	
Total Gate Charge	Qg	_	17	_		$V_{DS} = 50V, V_{GS} = 10V, I_D = 2.9A$	
Gate-Source Charge	Q <sub>gs</sub>		3.8	_	nC		
Gate-Drain Charge	Q <sub>gd</sub>	_	5.4	_			
Turn-On Delay Time	t <sub>D(on)</sub>		4.9	_		$V_{DS} = 50V, V_{GS} = 10V,$ $I_D = 1.0 \text{ A}, R_G = 6.0\Omega$	
Turn-On Rise Time	tr	_	3.7	_			
Turn-Off Delay Time	t <sub>D(off)</sub>	_	18	_	ns		
Turn-Off Fall Time	t <sub>f</sub>	_	9.4	—	1		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	_	40.5		ns	$V_{GS} = 0V, I_{S} = 2.9A,$	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	_	62		nC	$dI/dt = 100A/\mu s$	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing. Notes:

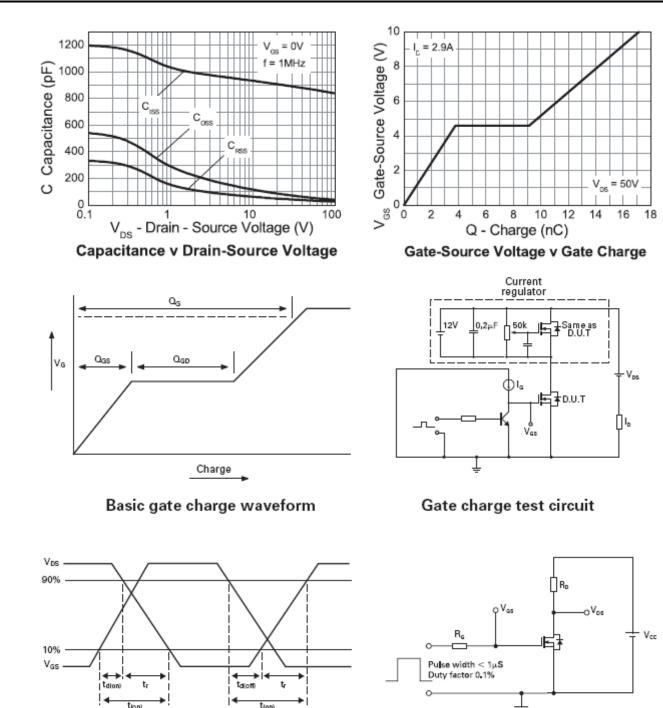


# **Typical Characteristics**





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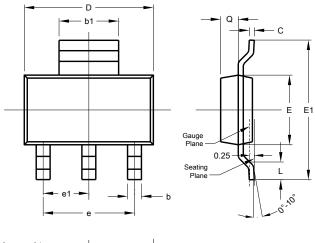
Switching time waveforms

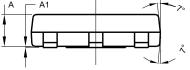
Switching time test circuit



# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

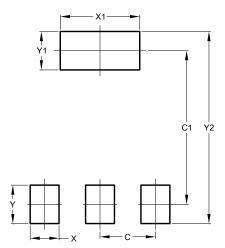




	SOT223					
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
E	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
AII	All Dimensions in mm					

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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